

1. Benefits

- Higher safety margin against overvoltage
- Improved efficiency all load conditions
- Increased efficiency compared to Silicon Diode alternatives
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway
- Essentially No Switching Losses

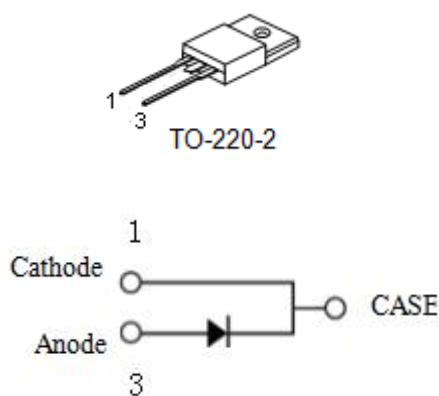
2. Features

- 650-Volt Schottky Rectifier
- Shorter recovery time
- High-speed switching possible
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Extremely Fast Switching
- Positive Temperature Coefficient on VF

3. Applications

- Switch Mode Power Supplies
- Power Factor Correction
- Motor Drives
- HID Lighting

4. Pin configuration



Pin	Function
1	Cathode
2	-
3	Anode

5. Absolute Maximum Ratings

($T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Rating	Units
Repetitive Peak Reverse Voltage	V_{RRM}	650	V
Surge Peak Reverse voltage	V_{RSM}	650	V
DC Blocking Voltage	V_{DC}	650	V
Continuous forward current			
$T_C = 25^\circ\text{C}$	I_F	24	A
$T_C = 135^\circ\text{C}$		11	
$T_C = 150^\circ\text{C}$		8	
Repetitive Peak Forward Current	I_{FRM}	56	A
Surge no repetitive forward current	I_{FSM}	72	A
Power Dissipation			
$T_C = 25^\circ\text{C}$	P_{tot}	107	W
$T_C = 110^\circ\text{C}$		46	
Operating Junction and storage temperature	T_J, T_{stg}	-55 to +175	°C

6. Thermal characteristics

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Thermal resistance	$R_{th(J-C)}$	-	-	2.8	-	°C/W

7. Electrical characteristics

Parameter	Symbol	Conditions		Rating			Unit
				Min	Typ	Max	
Gate Threshold Voltage	V_F	$I_F=8\text{A}$	$T_C=25^\circ\text{C}$	-	1.4	1.8	V
			$T_C=175^\circ\text{C}$	-	2.1	3	
Reverse Current	I_R	$V_R=650\text{V}$	$T_C=25^\circ\text{C}$	-	10	60	μA
			$T_C=175^\circ\text{C}$	-	48	500	
Total Capacitive Charge	Q_C	$VR = 400\text{V}, IF = 8\text{A}$ $T_J = 25^\circ\text{C}$ $Q_C = \frac{1}{2} C (V) dv$		-	25	-	nC
Total Capacitance	C	$T_J = 25^\circ\text{C}, f = 1\text{MHz}$	$V_R=0\text{V}$	-	440	-	pF
			$V_R=200\text{V}$		54		
			$V_R=400\text{V}$		40		
Capacitance Stored Energy	EC	$VR=400\text{V}$		-	5	-	μJ

8. Typical Characteristics

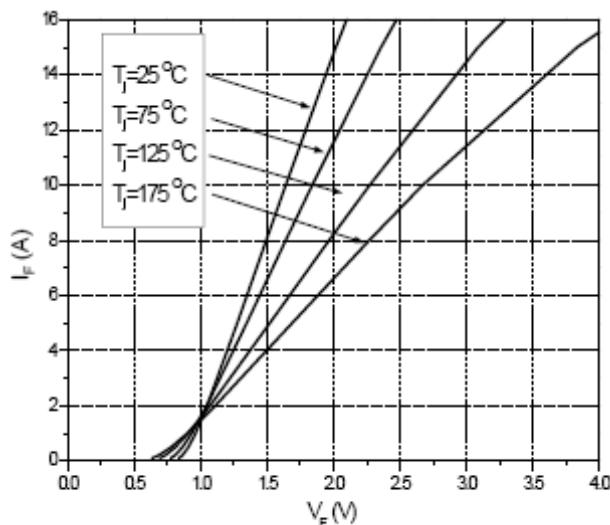


Figure 1. Forward Characteristics

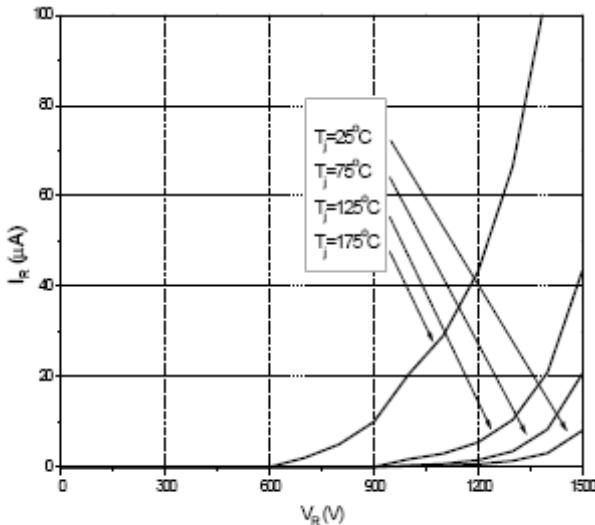


Figure 2. Reverse Characteristics

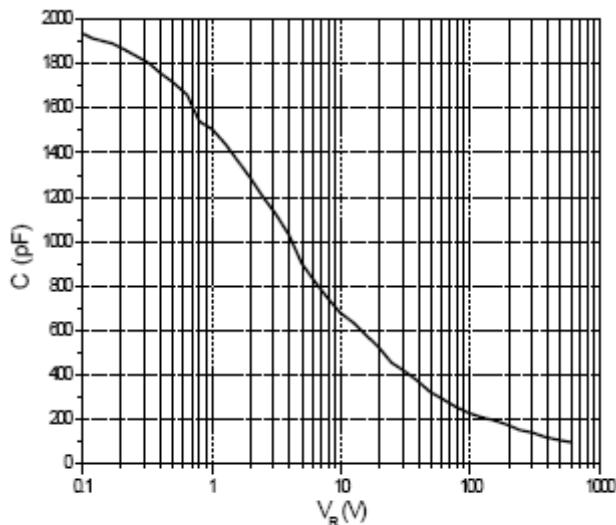


Figure 3. Capacitance vs. Reverse Voltage

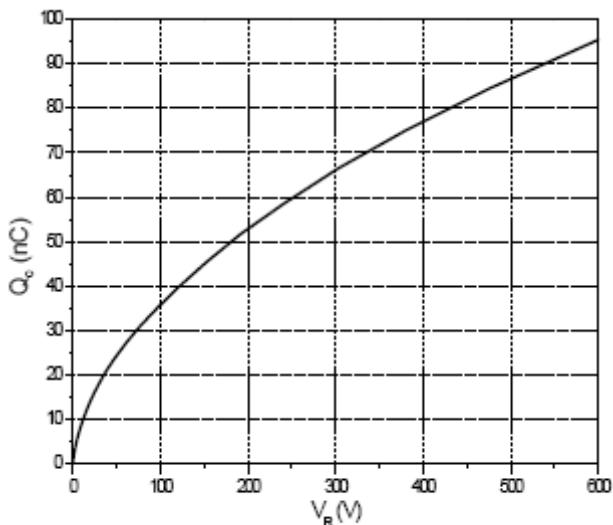


Figure 4. Total Capacitance Charge vs. Reverse Voltage

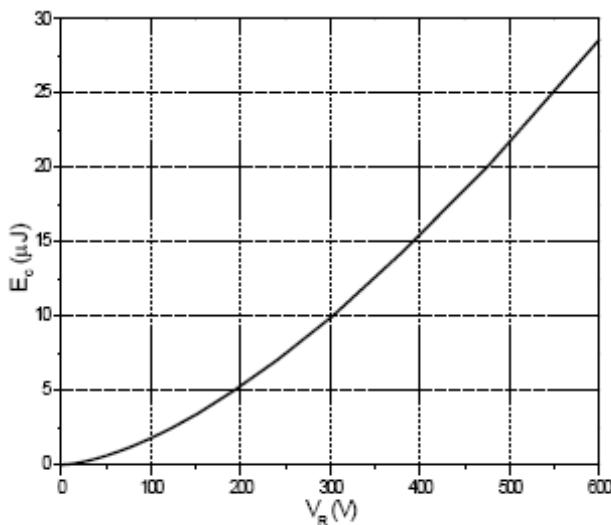


Figure 5. Capacitance Stored Energy